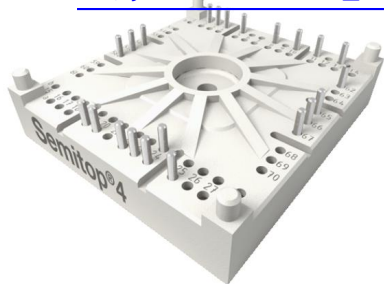


SK150GD066T

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SEMITOP® 4

IGBT Module

SK150GD066T

Target Data

Features

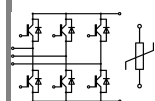
- One screw mounting module
- Fully compatible with SEMITOP®1,2,3
- Improved thermal performances by aluminium oxide substrate
- Trench IGBT technology
- CAL technology FWD
- Integrated NTC temperature sensor

Typical Applications

- Inverter up to 32 kVA
- Typ. motor power 15 kW

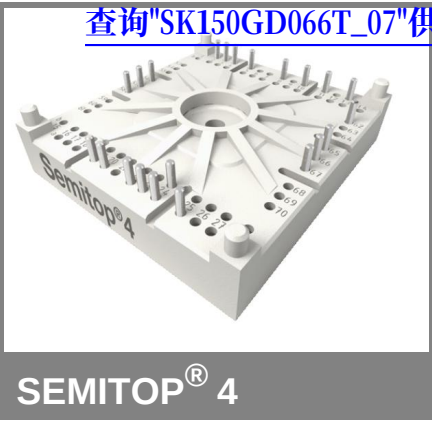
Absolute Maximum Ratings		$T_s = 25^\circ\text{C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
V_{CES}	$T_j = 25^\circ\text{C}$	600	V
I_C	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	151 A
		$T_s = 70^\circ\text{C}$	121 A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$	300	A
V_{GES}		± 20	V
t_{psc}	$V_{CC} = 360\text{ V}; V_{GE} \leq 20\text{ V}; T_j = 125^\circ\text{C}$ $V_{CES} < 600\text{ V}$	6	μs
Inverse Diode			
I_F	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	198 A
		$T_s = 70^\circ\text{C}$	152 A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	200	A
Module			
$I_{t(RMS)}$			A
T_{vj}		-40 ... +150	$^\circ\text{C}$
T_{stg}		-40 ... +125	$^\circ\text{C}$
V_{isol}	AC, 1 min.	2500	V

Characteristics			T _s = 25 °C, unless otherwise specified			
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 2,4 mA		5	5,8	6,5	V
I _{CES}	V _{GE} = 0 V, V _{CE} = V _{CES} T _j = 25 °C T _j = 125 °C					mA mA
I _{GES}	V _{CE} = 0 V, V _{GE} = 20 V T _j = 25 °C T _j = 125 °C		1200			nA nA
V _{CE0}	T _j = 25 °C T _j = 150 °C			0,8 0,7	1,1 1	V V
r _{CE}	V _{GE} = 15 V T _j = 25°C T _j = 150°C			4 6,5	5 7	mΩ mΩ
V _{CE(sat)}	I _{Cnom} = 150 A, V _{GE} = 15 V T _j = 25°C _{chiplev.} T _j = 150°C _{chiplev.}			1,45 1,65	1,85 2,05	V V
C _{ies} C _{oes} C _{res}	V _{CE} = 25, V _{GE} = 0 V f = 1 MHz			9,4 0,6 0,3		nF nF nF
t _{d(on)} t _r E _{on}	R _{Gon} = 16 Ω di/dt = 2400 A/μs	V _{CC} = 300V I _{Cnom} = 150A		127 117 11,8		ns ns mJ
t _{d(off)} t _f E _{off}	R _{Goff} = 16 Ω di/dt = 2400 A/μs	T _j = 125 °C V _{GE} = -7/+15 V		925 73 6,3		ns ns mJ
R _{th(j-s)}	per IGBT			0,55		K/W



GD-T

SK150GD066T



IGBT Module

SK150GD066T

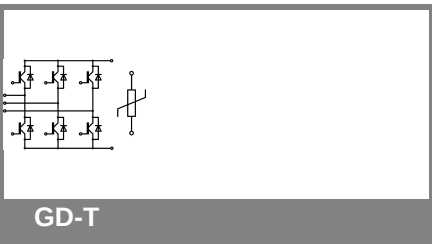
Target Data

Features

- One screw mounting module
- Fully compatible with SEMITOP®1,2,3
- Improved thermal performances by aluminium oxide substrate
- Trench IGBT technology
- CAL technology FWD
- Integrated NTC temperature sensor

Typical Applications

- Inverter up to 32 kVA
- Typ. motor power 15 kW

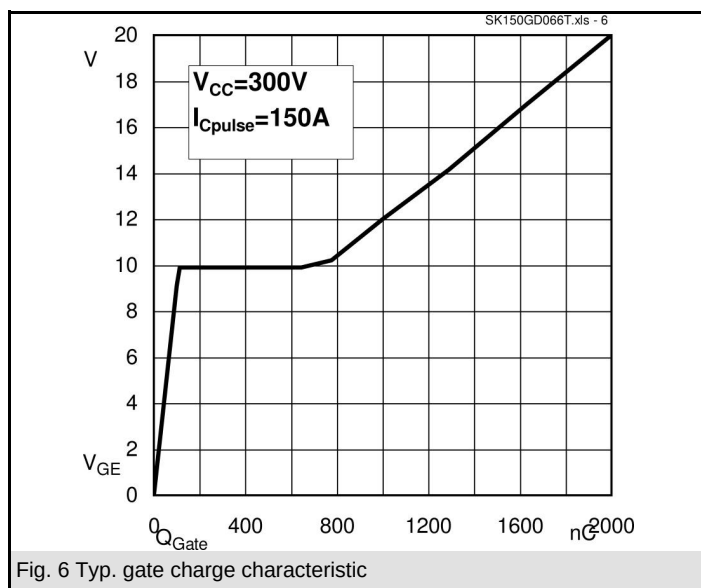
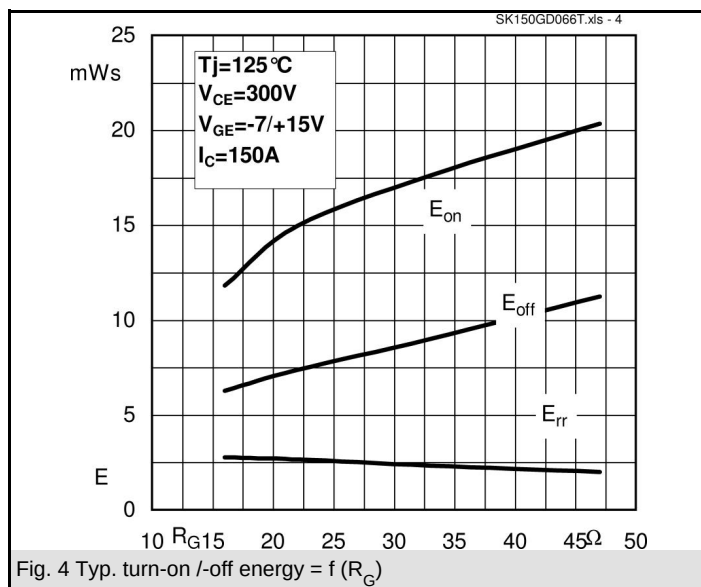
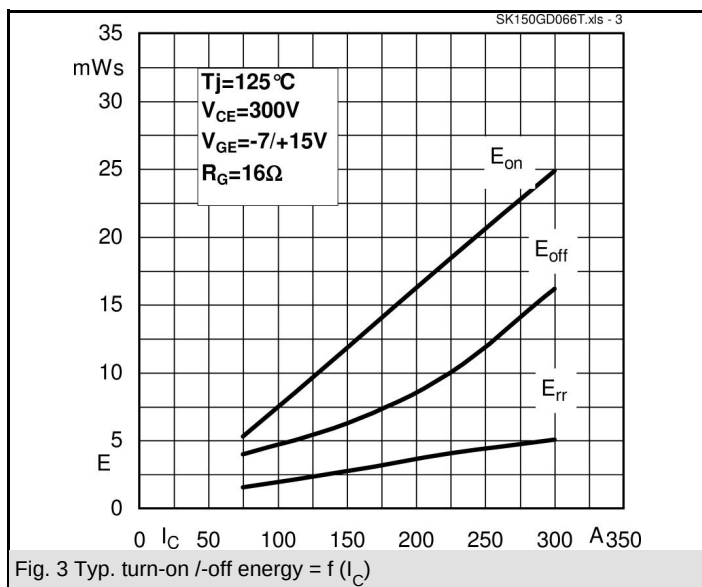
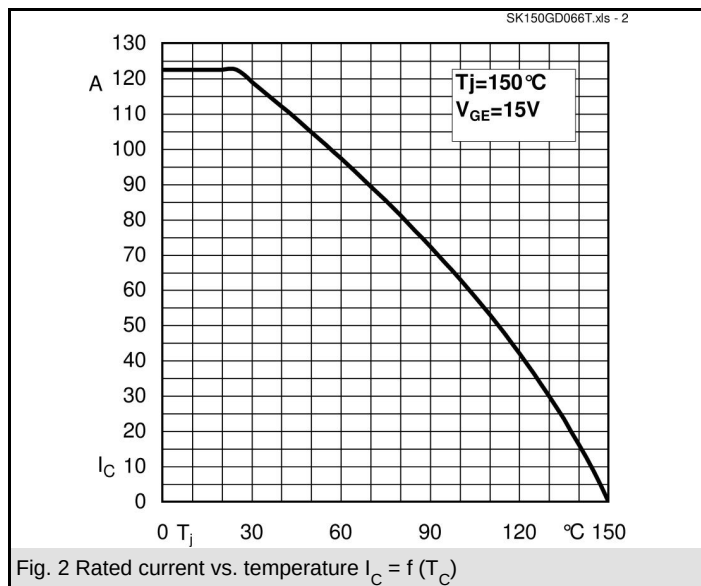
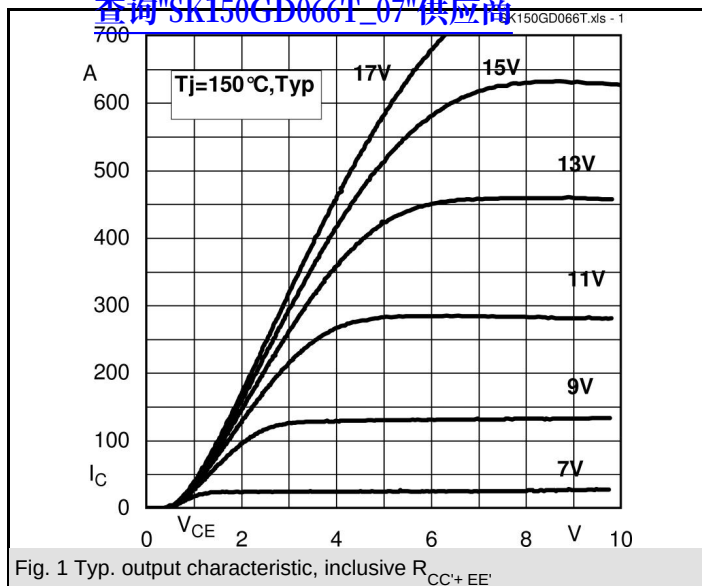


Characteristics						
Symbol	Conditions		min.	typ.	max.	Units
Inverse Diode						
V _F = V _{EC}	I _{Fnom} = 150 A; V _{GE} = 0 V	T _j = 25 °C _{chiplev.}		1,3		V
		T _j = 150 °C _{chiplev.}		1,2		V
V _{F0}		T _j = 25 °C		0,85		V
		T _j = 150 °C		0,9		V
r _F		T _j = 25 °C		3		mΩ
		T _j = 150 °C		2		mΩ
I _{RRM}	I _{Fnom} = 150 A	T _j = 125 °C		70		A
Q _{rr}	di/dt = 2400 A/μs			18		μC
E _{rr}	V _{CC} = 300V			2,75		mJ
R _{th(j-s)D}	per diode			0,54		K/W
M _s	to heat sink				3,5	Nm
w				60		g
Temperature sensor						
R ₁₀₀	T _s = 100°C (R ₂₅ =5kΩ)			493±5%		Ω

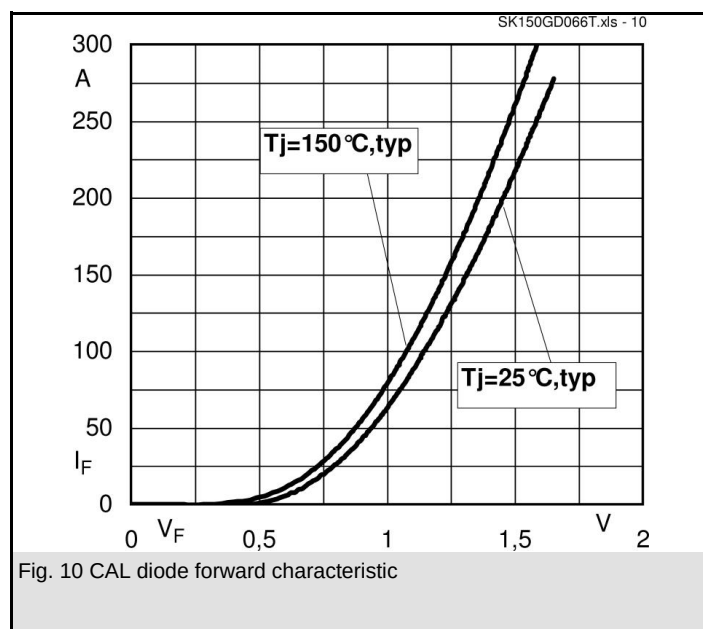
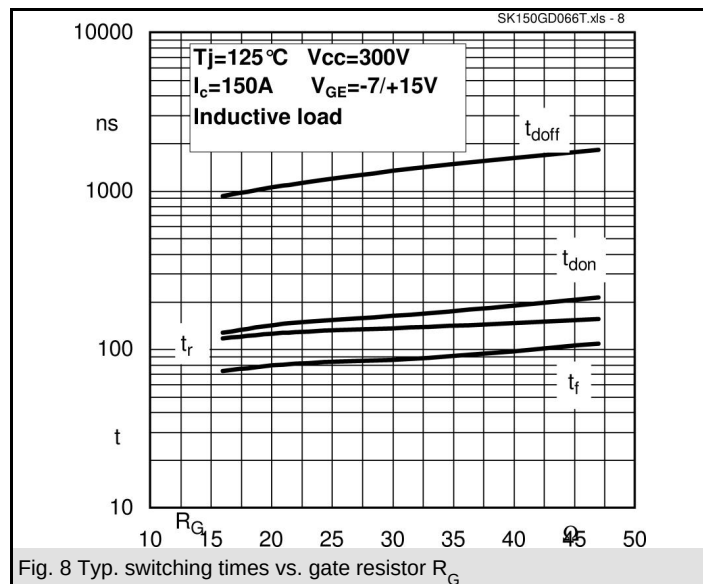
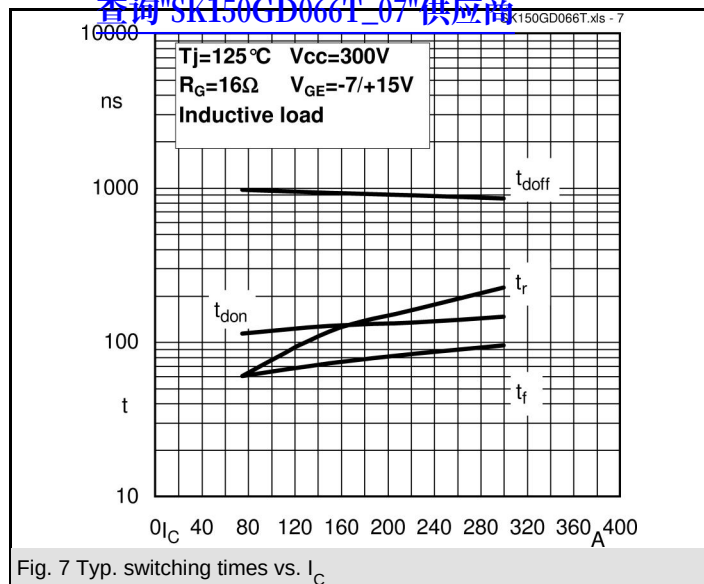
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

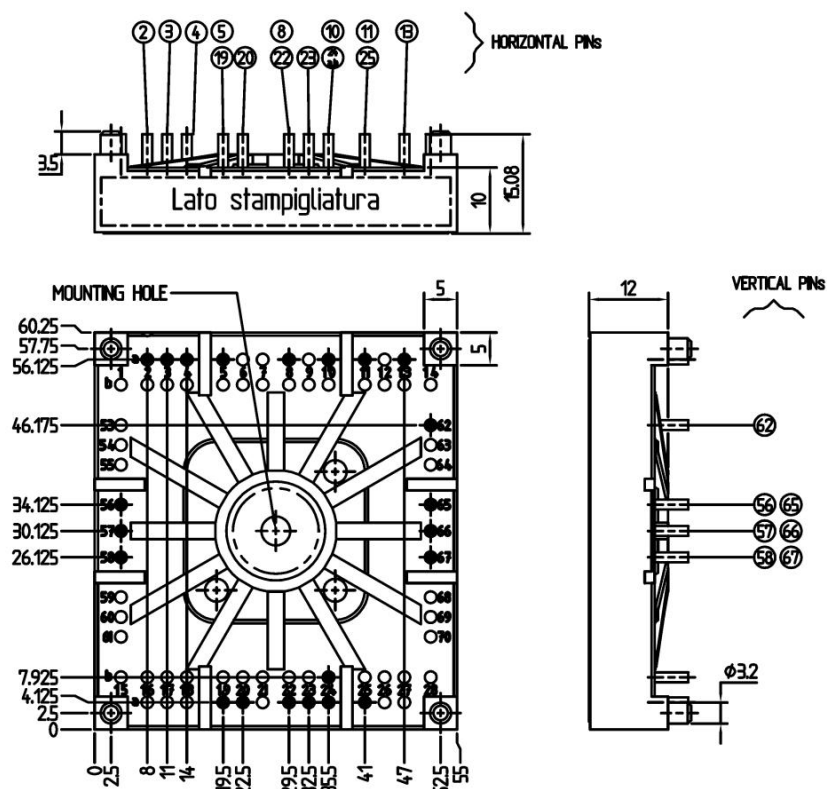
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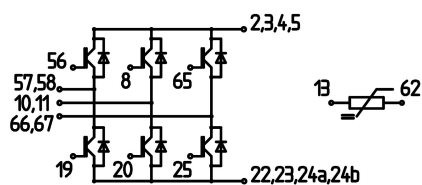
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Case T74 (Suggested hole diameter for the solder pins in the circuit board: 2mm. Suggested hole diameter for the mounting pins in the circuit board: 3,6mm)



Case T 74

GD-T